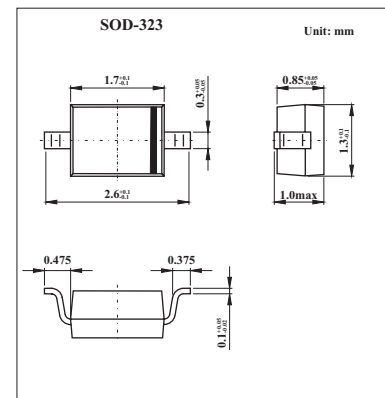


Silicon Epitaxial Planar Diode

1SV276

■ Features

- High Capacitance Ratio: $C_{1V}/C_{4V} = 2.0$ (Typ.)
- Low Series Resistance: $r_s = 0.22 \Omega$ (Typ.)

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	10	V
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse Voltage	V_R	$I_R = 1 \mu\text{A}$	10			V
Reverse Current	I_R	$V_R = 10 \text{V}$			3	nA
Capacitance	C_{1V}	$f = 1 \text{MHz}; V_R = 1 \text{V}$	15	16	17	pF
	C_{4V}	$f = 1 \text{MHz}; V_R = 4 \text{V}$	7	8	8.5	
Capacitance Ratio	C_{1V}/C_{4V}		1.8	2.0		
Series Resistance	r_s	$V_R = 1 \text{V}, f = 470 \text{MHz}$		0.22	0.4	Ω

■ Marking

Marking	TL
---------	----